

**Serial No.**

**INFORMATION DISCLOSURE  
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**160-386**

**10/609,410**

**Applicant**

**NAKAMURA et al.**

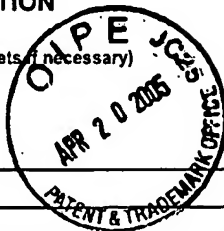
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## U.S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

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**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
VY	5,369,289	11/1994	Tamaki			
	5,247,533	9/1993	Okazaki et al			
	4,495,514	1/1985	Lawrence et al			
	5,281,830	1/1994	Kotaki et al			
	4,153,905	5/1979	Charmakadze et al			
VY	5,285,078	2/1994	Mimura et al			

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DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
VY 03-218625	9/1991	Japan			abs
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61-144859	9/1988	Japan			abs
63-61161	4/1988	Japan			abs
61-87381	5/1986	Japan			abs
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59228776	12/1984	Japan			abs
55009442 A	1/1980	Japan			abs
1990-0701577	7/1990	Korea			abs
5-211347	8/1993	Japan			abs
3-183173	8/1991	Japan			abs
4-68579	3/1992	Japan			abs
5-129658	5/1993	Japan			abs
57-111076	7/1982	Japan			abs
5-13816	1/1993	Japan			abs
62-2675	1/1987	Japan			X
62-287675	12/1987	Japan			abs
83103775	4/1994	Taiwan			X
7-45867	2/1995	Japan			abs
5-291621	11/1993	Japan			abs
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YES NO

✓	6-38265	5/94	Japan	—	Abs	
✓	62-101090	5/87	Japan	—	Abs	
✓	10-0225612	7/99	Korea	—	Abs	
✓	2-68968	3/90	Japan	—	Abs	

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✓	Oyo Buturi Vol. 60, No. 2, 1991 02; p. 164
✓	Hayes et al Proceedings of Symposium B 1990 Extended Abstracts EA-21 Electronic Optical and Device Properties of Layered Structures
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	Foresi et al "Metal contacts to gallium nitride" Appl. Phys. Letts 62 (1993 31 May No. 22, pp. 2859-2861
	Akasaki et al "High efficiency UV..." Proc. of the SPIE, Phys. Concepts of Materials...28 Oct. 1990, Aachen, DE, pp 138-149
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	H. Morkoc et al "Large-band-gap SiC..." J. Phys. 76(3), 1 Aug. 1994 pp 1363-1398
	Patent Abstracts of Japan, vol 18 no 80 (E-1505) 9 Feb 1994 & JP-A-05 291 621 (Nichia Chem Inc Ltd.) 5 Nov. 1993 (see abstract.
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✓	Database WPI, Week 9438, Derwent Publications Ltd. London GV An 94-308360 & JP A 6 237 012 (Nichia Kagaku Kogyo KK) 23 Au. 1994, see abstract

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